

Charge collection studies on heavily irradiated diodes from the RD50 multiplication run

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Special diodes were designed on RD50 multiplication mask which combine the ease of use of a pad-detector with electric field of a strip detector. A series of charge collection measurements was performed with diodes of different implant properties and thicknesses. The diodes were irradiated in steps with neutrons to the total accumulated fluence of $1e16$ cm⁻². Charge collection efficiency for ⁹⁰Sr was measured at each fluence step and the values were compared between the wafers with different properties.

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